**Draft for Public Comment**

Form 36

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Responsible committee: EPL/47 Semiconductors

Interested committees:

Title: BS EN IEC 63550-1 Semiconductor devices - Neuromorphic devices

Part 1: Evaluation method of basic characteristics in memristor devices

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**Introduction**

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For international standards, comments will be reviewed by the relevant UK national committee before sending the consensus UK vote and comments to the international committee, which will then decide appropriate action. If the international standard is approved, it is usual for the text to be published as a British Standard.

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**Template for comments and secretariat observations**

| Date: xx/xx/20xx | Document: ISO/DIS xxxx |
|---|---|

| 1 | 2 | (3) | 4 | 5 | (6) | 7 |
|---|---|---|---|---|---|---|
| **MB** | Clause No./ Subclause No./Annex **(e.g. 3.1)** | Paragraph/Figure/ Table/Note | **Type of comment** | **Commend (justification for change) by the MB** | **Proposed change by the MB** | **Secretariat observations on each comment submitted** |
| | 3.1 | Definition 1 | ed | Definition is ambiguous and needs clarifying. | Amend to read '...so that the mains connector to which no connection...' | |
| | 6.4 | Paragraph 2 | te | The use of the UV photometer as an alternative cannot be supported as serious problems have been encountered in its use in the UK. | Delete reference to UV photometer. | |

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# 47/2870/CD

COMMITTEE DRAFT (CD)

| | |
|---|---|
| PROJECT NUMBER: **IEC 63550-1 ED1** | |
| DATE OF CIRCULATION: **2024-08-30** | CLOSING DATE FOR COMMENTS: **2024-11-22** |
| SUPERSEDES DOCUMENTS: **47/2810/NP, 47/2833/RVN** | |

| | |
|---|---|
| IEC TC 47 : SEMICONDUCTOR DEVICES | |
| SECRETARIAT: Korea, Republic of | SECRETARY: Mr Cheolung Cha |
| OF INTEREST TO THE FOLLOWING COMMITTEES: | HORIZONTAL FUNCTION(S): |
| ASPECTS CONCERNED: | |

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TITLE:

**Semiconductor devices - Neuromorphic devices - Part 1: Evaluation method of basic characteristics in memristor devices**

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# CONTENTS

FOREWORD ..... 3
INTRODUCTION ..... 5
1 Scope ..... 7
2 Normative references ..... 7
3 Terms and definitions ..... 7
4 Device under test (DUT) ..... 9
4.1 General ..... 9
5. Test apparatus and environment ..... 9
5.1 General ..... 9
5.2 Test equipment and tools ..... 9
5.3 Probe station ..... 10
5.4 Test environment ..... 11
6. Test method ..... 11
6.1.1 Read ..... 11
6.1.2 Forming ..... 11
6.1.3 Initialize ..... 12
6.1.4 Potentiation programming ..... 13
6.1.5 Depression programming ..... 14
Test Report ..... 16
Bibliography ..... 17

Figure 1 – (a) A general neural network with neurons arranged in layers, with each layer's neurons connected to the layer before it and the one after it through synapses. (b) illustrative sketch of biological neurons and artificial neural system based on memristor ..... 6
Figure 2 – (a) The equivalent circuit of a memristor device (b) Schematic of memristor device. ..... 9
Figure 3 – Block diagram of the measurement setup of a memristor device ..... 10
Figure 4 – (a) Circuit diagram for read process (b) Voltage-time graph to exhibit the read operation of a memristor device ..... 11_Toc138532389
Figure 5 – (a) Circuit diagram in forming process (b) Voltage-time graph to exhibit the forming operation of a memristor ..... 12
Figure 6 – Simulation test flow chart of the forming process ..... 12
Figure 7 – Simulation test flow chart of the initialize operation of a memristor device ..... 13
Figure 8 – (a) Circuit diagram for forming process (b) Voltage-time graph to exhibit the potentiation operation of a memristor ..... 14
Figure 9 – Simulation test flow chart of the potentiation operation of a memristor ..... 14
Figure 10 – (a) Circuit diagram for forming process (b) Voltage-time graph to exhibit the depression operation of a memristor ..... 14
Figure 11 – Simulation test flow chart of the depression operation of a memristor ..... 15
Figure 12 – Exemplary cumulative resistance distribution after the potentiation and depression programming of a memristor device ..... 15

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# SEMICONDUCTOR DEVICES –

# Neuromorphic devices – Part 1: Evaluation method of basic characteristics in memristor devices

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International Standard IEC 62951-X has been prepared by technical committee 47: Semiconductor devices.

The text of this International Standard is based on the following documents:

| NP | Report on voting |
|---|---|
| 47/XX/NP | 47/XX/NP |

Full information on the voting for the approval of this standard can be found in the report on voting indicated in the above table.

The language used for the development of this International Standard is English.

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